

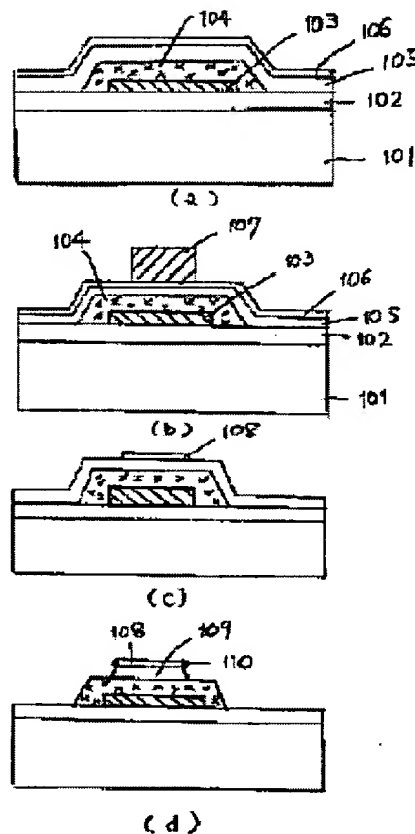
MANUFACTURE OF SEMICONDUCTOR DEVICE

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- international: **G11C11/22; H01G4/06; H01G7/06; H01L21/28; H01L27/04; G11C11/22; H01G4/06; H01G7/00; H01L21/02; H01L27/04; (IPC1-7): G11C11/22; H01G4/06; H01G7/06; H01L21/28; H01L27/04**
- european:
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Abstract of JP5089662

PURPOSE:To prevent Pt from adhering again and to enhance the quality of a Pt pattern by a method wherein a first thin film such as Pt is etched by making use of a second conductive film composed of Ti or the like as a mask.
CONSTITUTION:An insulating film 102, a ferroelectric-capacitor Pt electrode 103 and a PZT ferroelectric 104 are formed on an Si substrate 101 by a prescribed method. Then, a ferroelectric-capacitor Pt electrode 105 and Ti 106 are laminated; the Ti 106 is etched by making use of a resist 107 as a mask; a prescribed Ti pattern 108 is formed. In addition, by making use of it as a mask, the Pt layer 105 is etched; a Pt pattern 109 is obtained. When Ti whose etch rate is slower than that of Pt is used as a mask and an etched operation is executed, it is possible to prevent the Pt from adhering again and to from the Pt pattern which is good.



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